OC-X87XXXXX-X Series

Micro-miniature OCXO

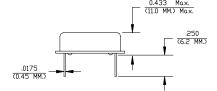
Rev. P

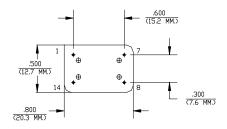
Features

- Low Cost DIL 14 package
- High Vacuum Sealed Crystal
- Low Power Consumption (500 mW)
- Fast Warm-up Time (2 minutes)
- Stratum3 or better Stability
- Low Aging < 3 ppm over life
- Very Low Phase Noise (-155dBc/Hz TYP)
- HCMOS/TTL or Sine-Wave output
- 8 MHz to 160 MHz Frequencies Available
- Voltage Control Optional
- Good Performance
- COTS/Dual use

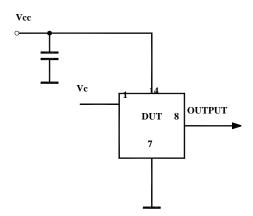
Applications

- Telecommunications
- Data Communications
- Instrumentation





ALL DIMENSIONS ARE TYPICAL UNLESS OTHERWISE NOTED





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CRYSTAL OSCILLATORS

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Specifications:

Parameter	Symb	Condition	Min	Тур	Max	Unit	Note	
Absolute Maximum Ratings								
Input Break	Vcc		-0.5		5.5	V	3.3V or 5V V	/cc
Down Voltage								
Storage temper.	Ts		-40		85	°C		
Control Voltage	Vc		-1		6	V		
Electrical (3)								
Frequency	F		8	10.000	160	MHz	1*	
Frequency stability	$\Delta F/F$	vs. Temp.		±100	±280	ppb	See chart below	
		vs. Supply		10	50	ppb/V		
Aging		per day		5E-9			after 30 days	
		first year		3E-7				Hz
		15 years			3E-6			Σ
Allan Deviation		.1s to 100s		5E-11				.10
Calibration		No voltage control		± 0.5	± 2	ppm		for
Vcc sensitivity				5E-8/V				ers
Load sensitivity		For 10% change			5E-8			All parameters for 10 MHz
SSB Phase Noise		10 Hz		-100		dBc/Hz	2*	araı
		100 Hz		-130				1 ps
		1 KHz		-140				A1
		10 KHz		-150				
		>100 KHz		-155				
Retrace		After 30 minutes			±100	ppb		
G-sensitivity		worst direction			±2.0	ppb/G		
Input Voltage	Vcc		4.75	5.0	5.25	V	See chart bel	ow
			3.15	3.3	3.45			
Power consumption	P	steady state, 25°C		0.5	0.7	W	Upper operat	ing
		steady state, -30°C			1.5		temperature < 70 20% for UOT	
Load				CMOS Outp				
Loau		Internally AC co		Ohm			Sine-wave ou	
Warm-up time	τ	to 0.3 ppm accuracy	upica 50	2	3	min	Sinc-wave ou	tput
Sub-Harmonics	· ·	to 0.5 ppin accuracy		-50	-40	dBc	At higher F	1*
Output Waveform		3 3V HCMOS/TT	L. compa	tible 4 ns			See chart bel	
output waveform		3.3V HCMOS/TTL compatible, 4 ns Tr/Tf, 40/60% duty cycle Sine-wave, + 7 dBm ±3 dBm into 50 Ohm, -30 dBc harmonics				See chart below		
Control voltage	Vc	,	0		4.0	V		
Pull range		from nominal F	±5	±10		ppm	Customer spec	ified
Deviation slope		Monotonic, posit		5		ppm/V	Customer specified	
Setability	Vc0	@25°C, Fnom.	1.0	2.0	3.0	V	5V/3.3 supply	
Modulation	Fm	,	DC		1	KHz	Note 4	
Bandwidth								
Environmental and Mechanical								
0		200C t- 700C Ct	. JJ. O4					

Zivvi otinomat ana riconamon		
Operating temp. range	-30°C to 70°C Standard, Other options – see chart below	
Mechanical Shock	Per MIL-STD-202, 30G, 11ms	
Vibration	Per MIL-STD-202, 5G to 2000 Hz	
Soldering Conditions	Leads Temperature 260°C, for 10s, Max	
Hermetic Seal	Leak rate less than 1x10 ⁻⁸ atm.ccm/s of helium	

Electrical Connections

Pin Out	Pin 1- Vc; Pin 7- Case, GND; Pin8 – Output; Pin 14 - Vcc
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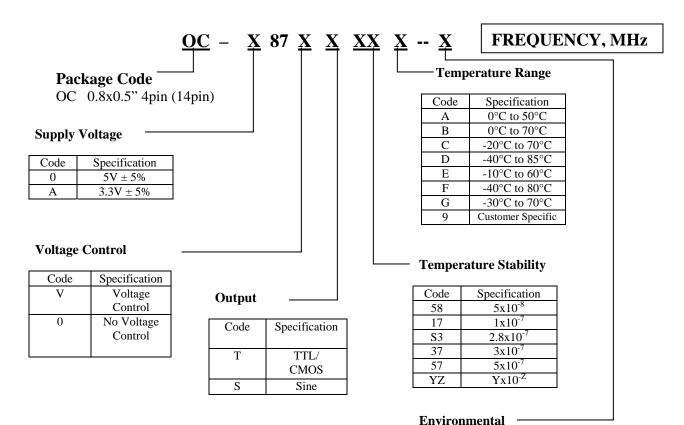
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Creating a Part Number



Not all combinations are available. Consult Factory.

Code	Specification
L	Contains a level of lead
	that is in excess of
	RoHS directive and is
	not designed for reflow
R	RoHS compliant, not
	designed for reflow

Notes:

- 1* Higher frequencies can be achieved either by using higher frequency crystals or by low noise analog harmonic multiplication. Both methods have advantages and drawbacks. If lowest possible phase noise on the noise floor is most important high frequency crystal will be used. If phase noise close to the carrier and aging are more important multiplication will be used. Please consult factory for your specific requirement.
- 2* Phase noise deteriorates with frequencies going higher. If analog multiplication is used to achieve higher frequency the phase noise roughly follows the formula of additional 20LogN, where N is a multiplication factor across entire frequency offset range. If higher frequency is achieved by using higher frequency crystal phase noise close to the carrier deteriorates due to the lower Q of the crystal and is usually worse, compared to multiplied solution. On the noise floor, however it remains more or less the same.
 - 3 All parameters, unless otherwise specified, are at nominal conditions, ie: T=25°C, Nominal Vcc & Nominal Load.
 - 4 Older and stock units may have MBW of 150 Hz Max.



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